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U.S. PTO

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U.S. UTILITY Patent Application

PATENT NUMBER and
ISSUE DATE

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10034163	12/27/2001	438	3	28123	S. FOONG

**APPLICANTS: Jeon Joong;

2823

**CONTINUING DATA VERIFIED:

** FOREIGN APPLICATIONS VERIFIED:

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>
Foreign priority claimed 35 USC 119 conditions met Verified and Acknowledged Examiner's initials		□ yes □ no □ yes □ no
ATTORNEY DOCKET NO G0518		
TITLE : Preparation of stack high-K gate dielectrics with nitrided layer		
U.S. DEPT. OF COMM./PAT. & TM-PTO-436L (Rev. 12-94)		

NOTICE OF ALLOWANCE MAILED		Assistant Examiner	CLAIMS ALLOWED	
			Total Claims	Print Claim for O.G
ISSUE FEE		DRAWING		
Amount Due	Date Paid	Sheets Drwg.	Figs.Drwg.	
<input type="checkbox"/> TERMINAL DISCLAIMER		Print Fig.		
		Application Examiner		
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